

**AMENDMENTS TO THE CLAIMS**

1 (currently amended). A semiconductor laser device comprising: a stem body having a reference surface; a heat radiation block which is provided on the reference surface of the stem body and which has a semiconductor laser chip mounted on a side face thereof; and a lead which extends through the stem body, wherein

a portion of the lead protruding on a reference surface side is placed on one side surface side of the heat radiation block on which the semiconductor laser chip is mounted, and

the semiconductor laser device further comprises a cover which is fixed attached to at least one the side face of the heat radiation block at both ends thereof ~~and the stem body~~ so as to surround the semiconductor laser chip and the portion of the lead protruding on the reference-surface side, in conjunction with the side face of the heat radiation block, and which is opened on at least one side of the cover that is a beam-output side of the semiconductor laser chip.

2 (original). The semiconductor laser device according to Claim 1, wherein  
the cover is made of a resin material.

3 (original). The semiconductor laser device according to Claim 1, wherein  
a depth of the cover in the beam-output direction of the semiconductor laser chip is substantially equal to a depth of the heat radiation block.

4 (original). The semiconductor laser device according to Claim 1, wherein  
the cover has a recessed portion for putting therein a resin for bonding the cover to the heat radiation block.

5 (original). The semiconductor laser device according to Claim 1, wherein  
the heat radiation block has a recessed portion for putting therein a resin for bonding the cover to the heat radiation block.